

1. (Thrice Amended)

Sub E1
A method of manufacturing a thin film resistor with a moisture barrier comprising:

DI
depositing a non-tantalum metal film resistive layer on a thin film resistor substrate;
attaching a thin film resistor termination on each end of the metal film resistive layer; and
depositing the moisture barrier comprising a layer of tantalum pentoxide film directly overlaying
and attaching to the metal film resistive layer to reduce failures due to electrolytic
corrosion under powered moisture conditions.

15. (Twice Amended)

A method of manufacturing a thin film resistor with a moisture barrier comprising:

DI
Sub E2
depositing a non-tantalum metal film resistive layer on a substrate;
attaching a termination on each end of the metal film resistive layer;
depositing a passivation layer directly overlaying and attaching to the metal film layer; and
depositing the moisture barrier comprising a layer of tantalum pentoxide film directly overlaying
and attaching to the passivation layer for reducing failures due to electrolytic corrosion
under powered moisture conditions.